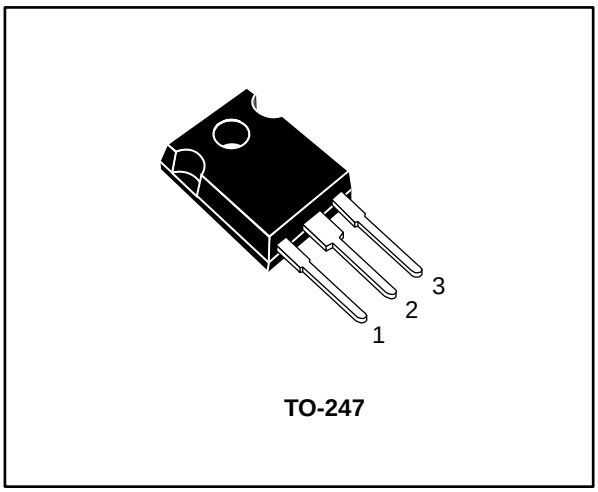
STW70N65M2

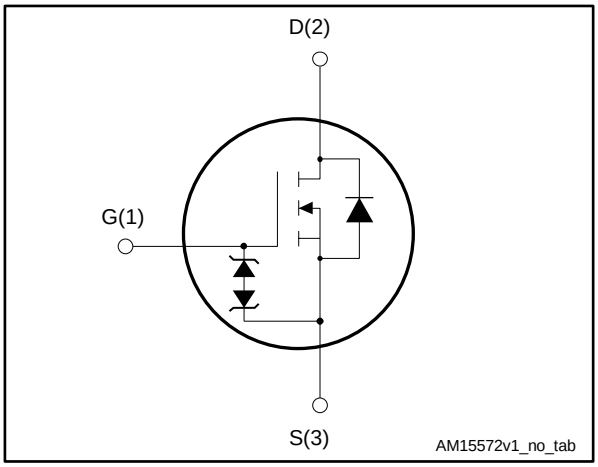
N-channel 650 V, 0.039 Ω typ., 63 A MDmesh™ M2 Power MOSFET in a TO-247 package

Datasheet - production data



TO-247

Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STW70N65M2	650 V	0.046 Ω	63 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STW70N65M2	70N65M2	TO-247	Tube

This is information on a product in full production.

Contents

1 Electrical ratings 3
2 Electrical characteristics 4
2.1 Electrical characteristics (curves) 6
3 Test circuits 8
4 Package mechanical data 9
4.1 TO-247 package information 9
5 Revision history 11

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	63	A
I_D	Drain current (continuous) at T_C= 100 °C	40	A
I_{DM} (1)	Drain current (pulsed)	252	A
P_{TOT}	Total dissipation at T_C = 25 °C	446	W
dv/dt (2)	Peak diode recovery voltage slope	15	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	- 55 to 150	°C
T_j	Operating junction temperature range		

Notes:

(1)Pulse width limited by safe operating area.

(2) $I_{SD} \leq 63$ A, di/dt ≤ 400 A/µs; $V_{DS\ peak} < V_{(BR)DSS}$, V_{DD} = 400 V

(3) $V_{DS} \leq 520$ V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	0.28	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient max	50	°C/W

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetetive or not repetetive (pulse width limited by T_{jmax})	4	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	3500	mJ

2 Electrical characteristics

(T_C= 25 °C unless otherwise specified)

Table 5: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	650			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 650 V			1	µA
		V_{GS} = 0 V, V_{DS} = 650 V, T_C = 125 °C (1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ± 25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 31.5 A		0.039	0.046	Ω

Notes:

(1)Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 100 V, f = 1 MHz, V_{GS} = 0 V	-	5140	-	pF
C_{oss}	Output capacitance		-	208	-	pF
C_{rss}	Reverse transfer capacitance		-	2.9	-	pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 V to 520 V, V_{GS} = 0 V	-	520	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D=0 A	-	3	-	Ω
Q_g	Total gate charge	V_{DD} = 520 V, I_D = 63 A, V_{GS} = 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	117	-	nC
Q_{gs}	Gate-source charge		-	21.5	-	nC
Q_{gd}	Gate-drain charge		-	51	-	nC

Notes:

(1)$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 325 V, I_D = 31.5 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14: "Test circuit for resistive load switching times"* and *Figure 19: "Switching time waveform"*)	-	24	-	ns
t_r	Rise time		-	22	-	ns
$t_{d(off)}$	Turn-off-delay time		-	134	-	ns
t_f	Fall time		-	11	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		63	A
I_{SDM} (1)	Source-drain current (pulsed)		-		252	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 63 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 63 A, di/dt = 100 A/µs, V_{DD} = 60 V (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	584		ns
Q_{rr}	Reverse recovery charge		-	14.5		µC
I_{RRM}	Reverse recovery current		-	50.5		A
t_{rr}	Reverse recovery time	I_{SD} = 63 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	725		ns
Q_{rr}	Reverse recovery charge		-	20		µC
I_{RRM}	Reverse recovery current		-	55.5		A

Notes:

(1)Pulse width is limited by safe operating area

(2)Pulse test: pulse duration = 300 µs, duty cycle 1.5%

2.2 Electrical characteristics (curves)

Figure 2: Safe operating area

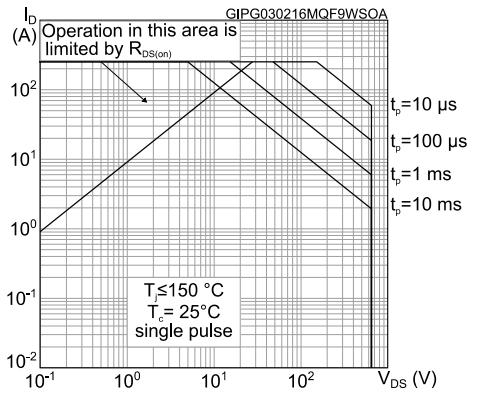


Figure 3: Thermal impedance

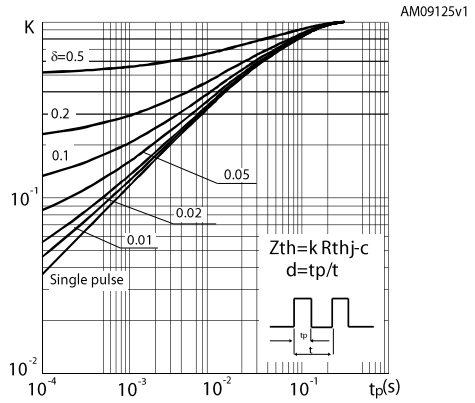


Figure 4: Output characteristics

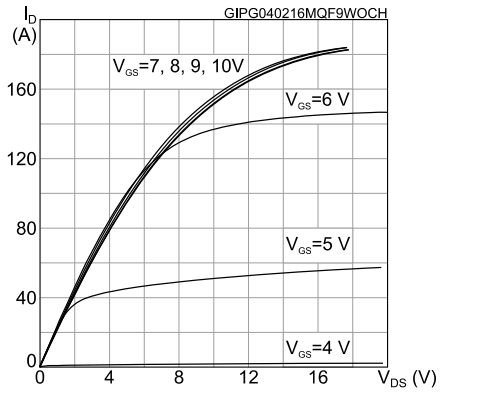


Figure 5: Transfer characteristics

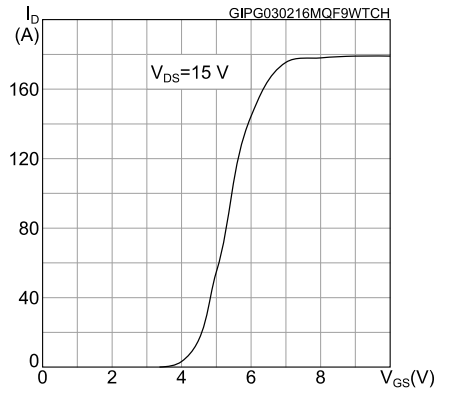


Figure 6: Gate charge vs. gate-source voltage

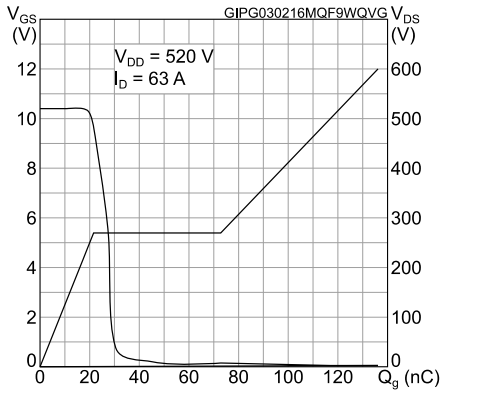


Figure 7: Static drain-source on-resistance

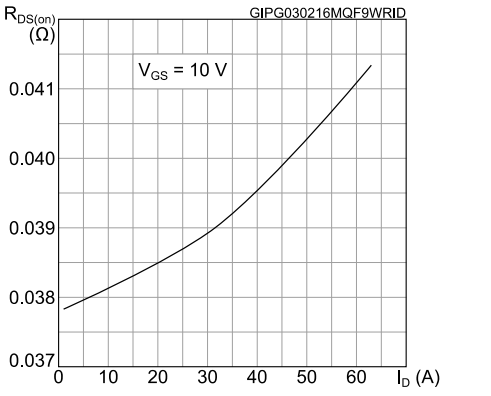


Figure 8: Capacitance variations

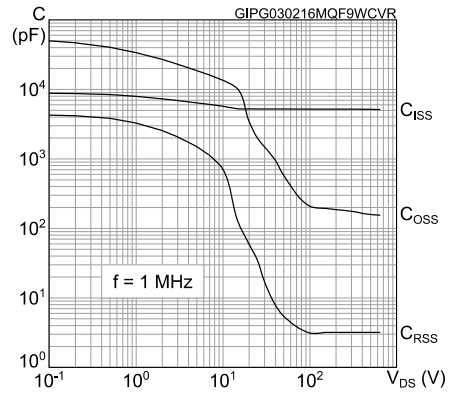


Figure 9: Normalized gate threshold voltage vs temperature

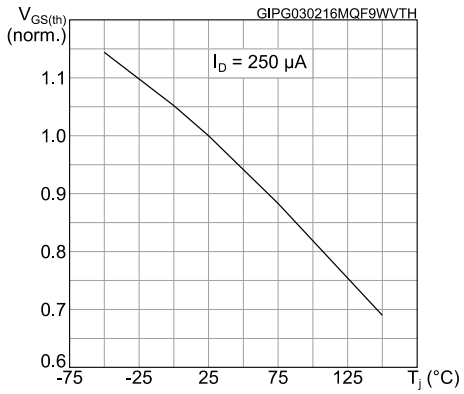


Figure 10: Normalized on-resistance vs temperature

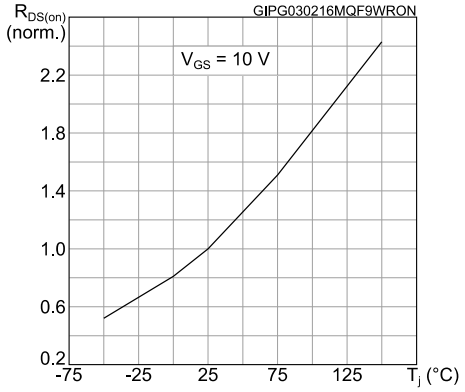


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

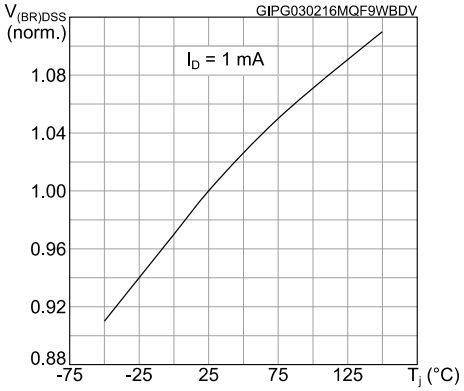


Figure 12: Output capacitance stored energy

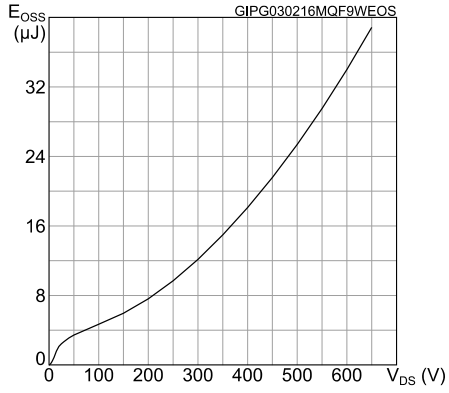
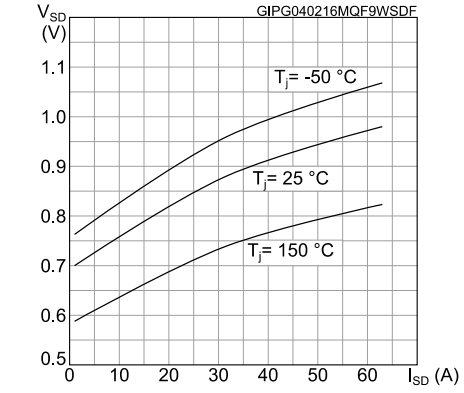


Figure 13: Source-drain diode forward characteristics



3 Test circuits

Figure 14: Test circuit for resistive load switching times

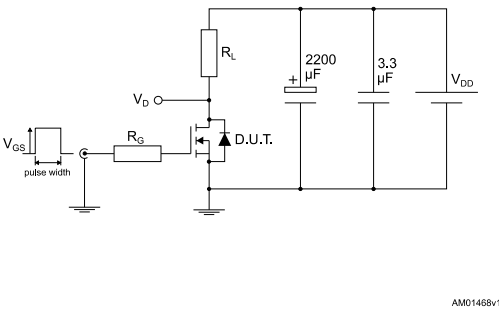


Figure 15: Test circuit for gate charge behavior

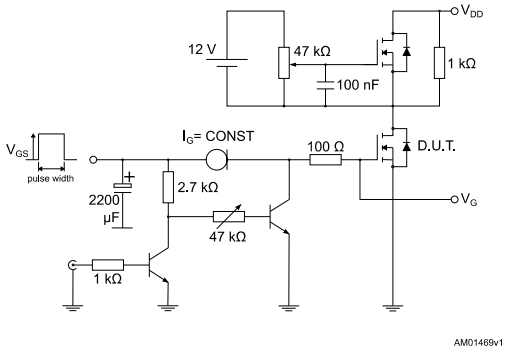


Figure 16: Test circuit for inductive load switching and diode recovery times

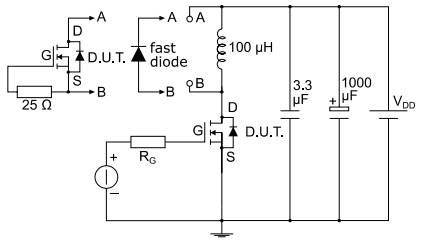


Figure 17: Unclamped inductive load test circuit

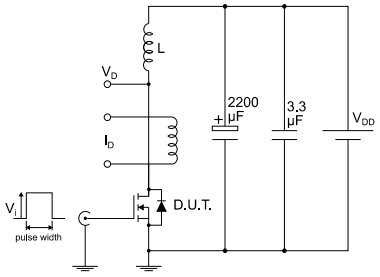


Figure 18: Unclamped inductive waveform

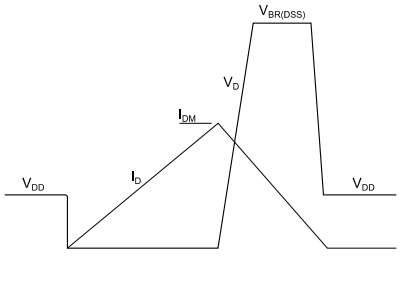
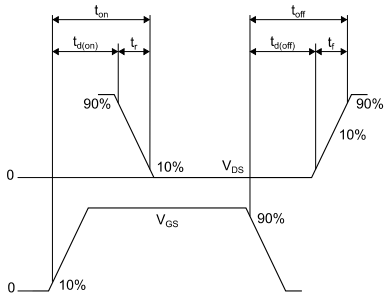


Figure 19: Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 TO-247 package information

Figure 20: TO-247 package outline

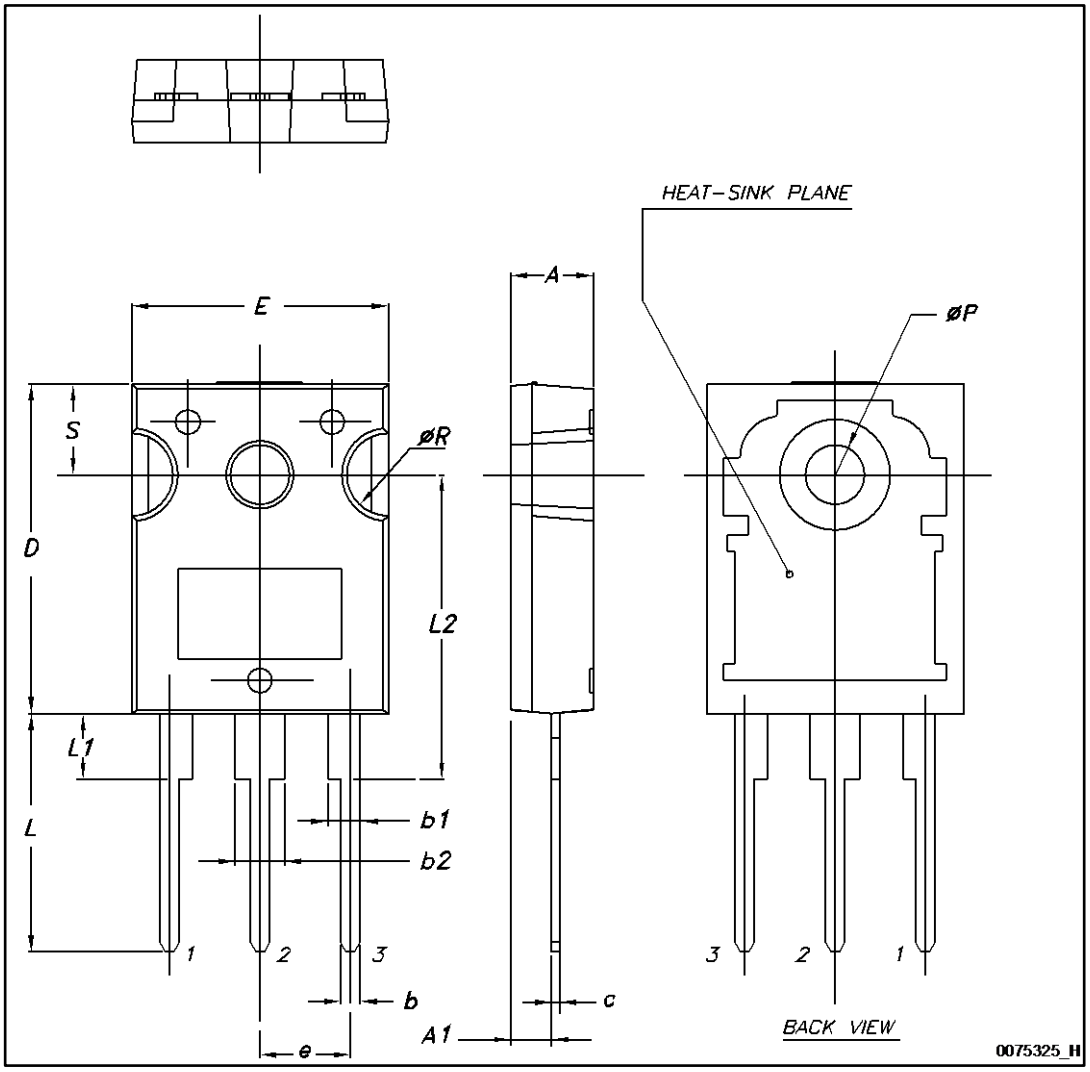


Table 9: TO-247 package mechanical data

Dim.	mm.		
	Min.	**Typ.**	**Max.**
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
04-Feb-2016	1	First release.

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